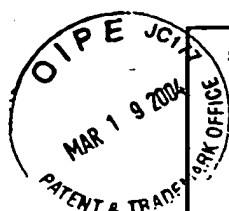


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				Application Number	10/716,455-Conf. #6664
				Filing Date	November 20, 2003
				First Named Inventor	Takashi Takahashi
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	R2184.0271/P271

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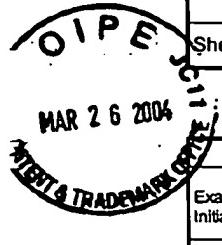
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
Sheet	1	of	2	Application Number	10716,455-Conf. #6664
				Filing Date	November 20, 2003
				First Named Inventor	Takashi Takahashi
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	R2184.0271/P271

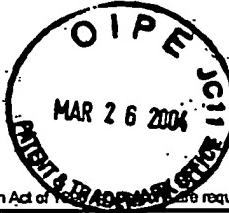


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NON PATENT LITERATURE DOCUMENTS					
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				10/716,455-Conf. #6664
(Use as many sheets as necessary)				Filing Date
Sheet	2	of	2	November 20, 2003
				First Named Inventor
				Takashi Takahashi
				Art Unit
				2811
				Examiner Name
				Not Yet Assigned
				Attorney Docket Number
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